



# FPF2C8P2NL07A F2, 3-phase, 3-level NPC module with Press-fit / NTC

### **General Description**

Fairchild's new inverter modules provide low conduction and switching loss as well. And Press-Fit technology provides simple and reliable mounting. These modules are optimized for the applications such as solar inverter and UPS where a high efficiency and robust design is needed.

#### **Electrical Features**

- High Efficiency
- Low Conduction and Switching Losses
- Field Stop IGBT for Inner and Outer Switch
- STEALTH<sup>TM</sup> Diode for Path Diode
- Built-in NTC for Temperature Monitoring

#### **Mechanical Features**

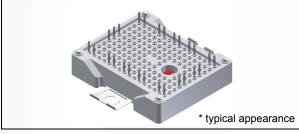
- Compact Size : F2 Package
- Press-fit Contact Technology
- Al<sub>2</sub>O<sub>3</sub> Substrate with Low Thermal Resistance

#### Applications

- Solar Inverter
- UPS

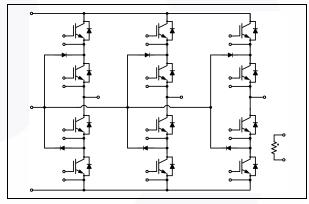
#### **Related Materials**

 AN-4167: Mounting Guideline for F1 / F2 Modules with Press-Fit Pins



Mar. 2015

Package Code: F2



Internal Circuit Diagram

## Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity / Tray
FPF2C8P2NL07A	FPF2C8P2NL07A	F2	Tray	14

Symbol	Descr	Rating	Units	
Outer IGBT	(Q1, Q4, Q5, Q8, Q9, Q12)			
V <sub>CES</sub>	Collector-Emitter Voltage	650	V	
V <sub>GES</sub>	Gate-Emitter Voltage		± 20	V
I <sub>C</sub>	Continuous Collector Current	@ T <sub>C</sub> = 80 °C, T <sub>Jmax</sub> = 175 °C	30	Α
I <sub>CM</sub>	Pulsed Collector Current	limited by T <sub>Jmax</sub>	60	A
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25 °C	135	W
TJ	Operating Junction Temperature		- 40 to + 150	°C
Inner IGBT	(Q2, Q3, Q6, Q7, Q10, Q11)			<u> </u>
V <sub>CES</sub>	Collector-Emitter Voltage		650	V
V <sub>GES</sub>	Gate-Emitter Voltage		± 20	V
I <sub>C</sub>	Continuous Collector Current	@ T <sub>C</sub> = 80 °C, T <sub>Jmax</sub> = 175 °C	50	Α
I <sub>CM</sub>	Pulsed Collector Current	limited by T <sub>Jmax</sub>	100	A
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25 °C	174	W
TJ	Operating Junction Temperature		- 40 to + 150	°C
Outer - Inne	er IGBT Series Connection			
SCWT	Short Circuit Withstand Time	V <sub>DC</sub> = 300 V, V <sub>GE</sub> = 15 V T <sub>C</sub> = 25 °C	4	μS
Diode				
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage		650	V
I <sub>F</sub>	Continuous Forward Current	@ T <sub>C</sub> = 80 °C, T <sub>Jmax</sub> = 175 °C	15	A
I <sub>FM</sub>	Maximum Forward Current		30	A
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25 °C	100	W
TJ	Operating Junction Temperature		- 40 to + 150	°C
Module				
T <sub>STG</sub>	Storage Temperature	- 40 to + 125	°C	
V <sub>ISO</sub>	Isolation Voltage @ AC 1 min.		2500	V
lsoMaterial	Internal Isolation Material	Al <sub>2</sub> O <sub>3</sub>		
T <sub>MOUNT</sub>	Mounting Torque	2.0 to 5.0	Nm	
Creepage	Terminal to Heat Sink	11.5	mm	
	Terminal to Terminal	6.3	mm	
Clearance	Terminal to Heat Sink	10.0	mm	
	Terminal to Terminal	5.0	mm	

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